



SEMIPACK®

Fast Diode Modules

SKKE 330F

Features

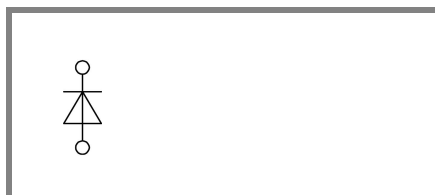
- CAL (controlled axial lifetime) chip technology, patent No. DE 43 10 44
- Heat transfer through aluminium oxide DCB ceramic isolated metal baseplate
- Small recovered charge
- Fast & soft recovery CAL diodes
- UL recognized, file no. E 63 532

Typical Applications

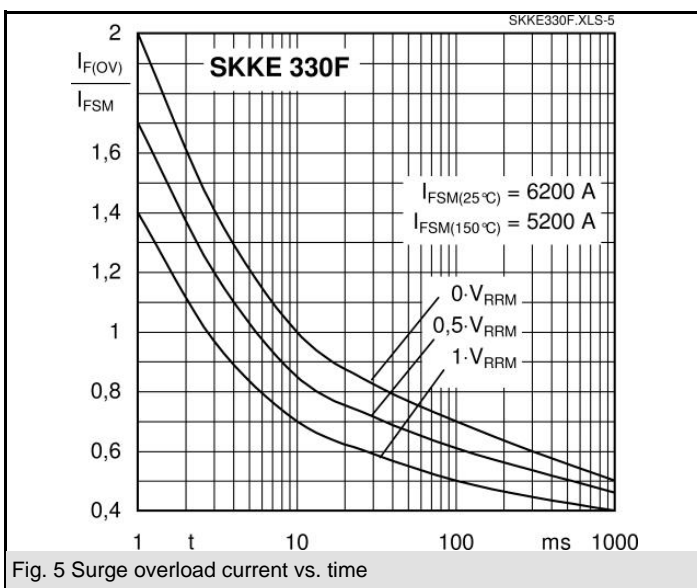
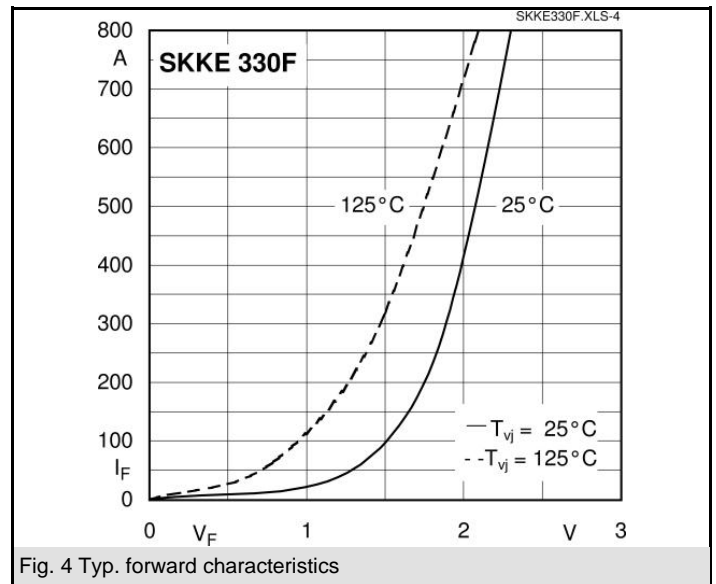
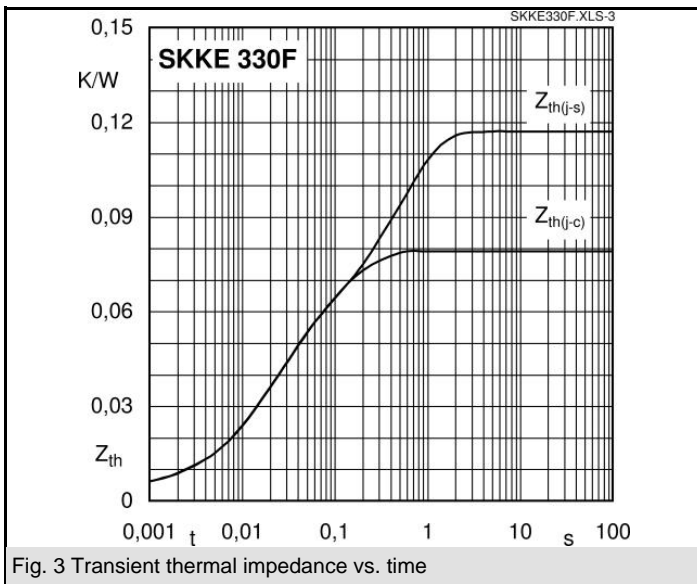
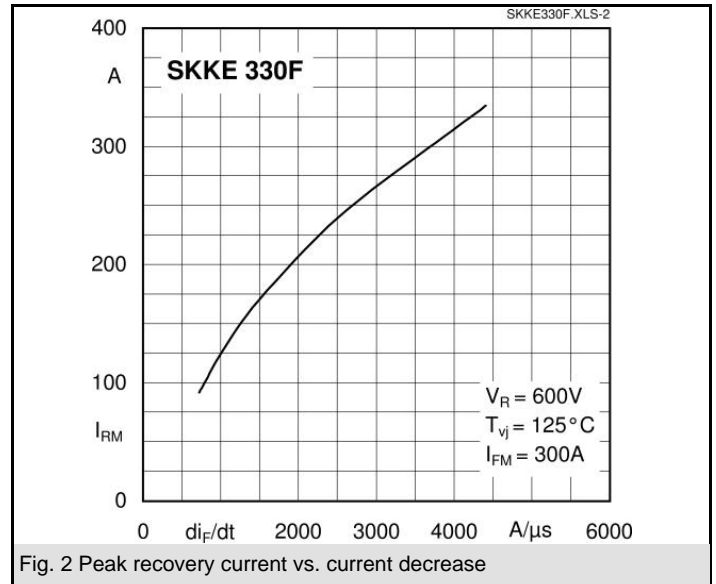
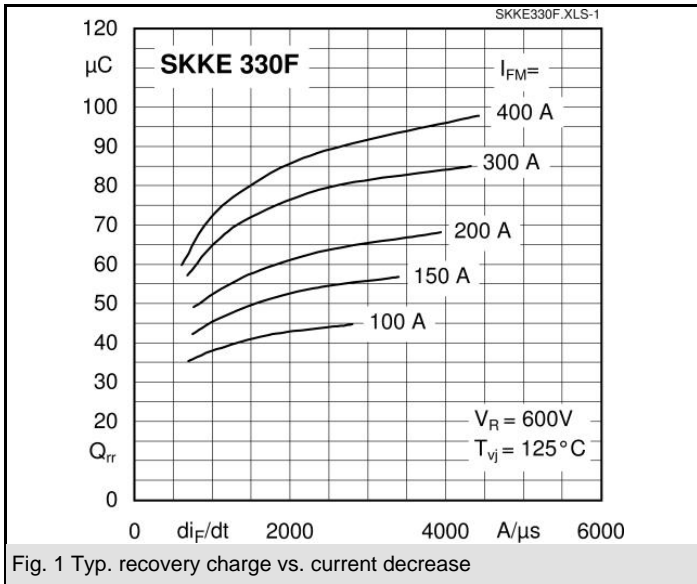
- Freewheeling diodes for IGBT
- Freewheeling diode for inductive loads
- Brake choppers
- Inverters and DC choppers
- AC motor control
- Boost choppers
- up to 20 kHz

V_{RSM} V	V_{RRM} V	$I_{FRMS} = 450$ A (maximum value for continuous operation)	
1700	1700	$I_{FAV} = 330$ A (sin. 180; 50 Hz; $T_c = 70$ °C)	
		SKKE 330F17	

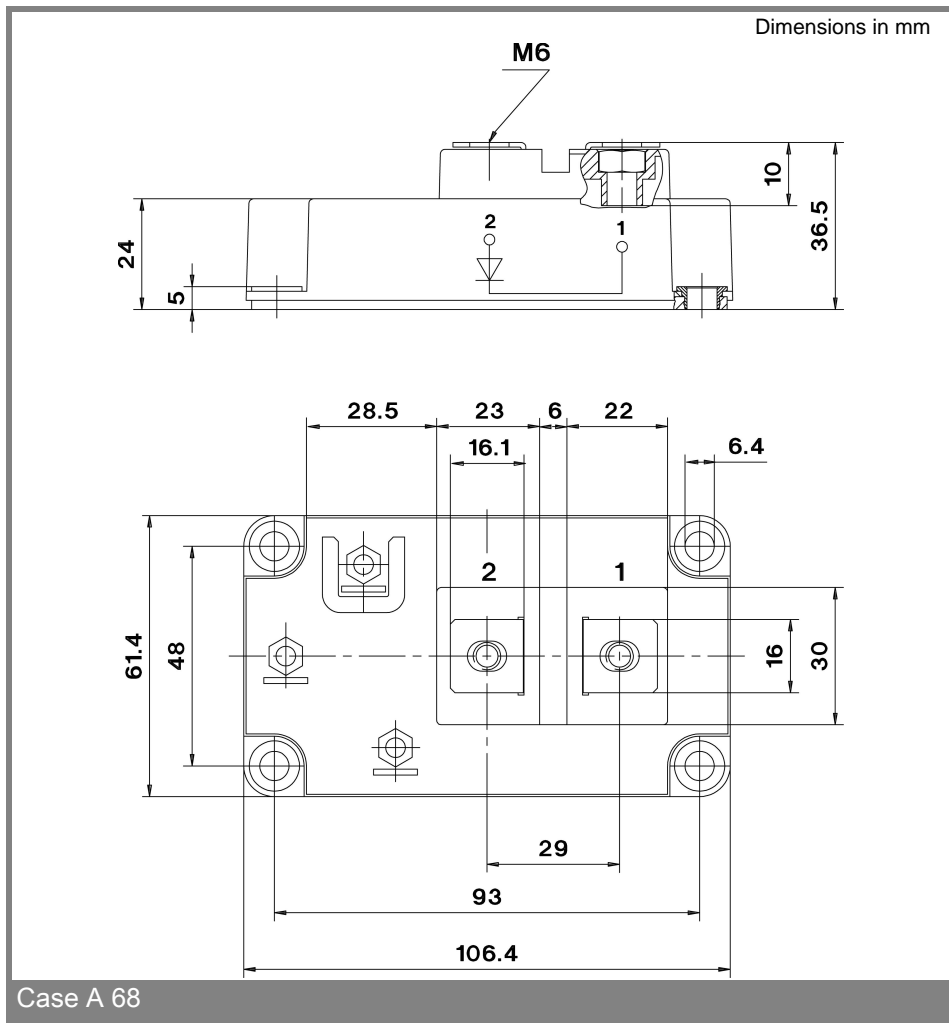
Symbol	Conditions	Values	Units
I_{FAV}	sin. 180; $T_c = 85$ (100) °C	290 (240)	A
I_{FSM}	$T_{vj} = 25$ °C; 10 ms	6200	A
	$T_{vj} = 150$ °C; 10 ms	5200	A
i^2t	$T_{vj} = 25$ °C; 8,3 ... 10 ms	192000	A ² s
	$T_{vj} = 150$ °C; 8,3 ... 10 ms	135000	A ² s
V_F	$T_{vj} = 25$ °C; $I_F = 330$ A	max. 2	V
$V_{(TO)}$	$T_{vj} = 150$ °C	max. 1,5	V
r_T	$T_{vj} = 150$ °C	max. 1,9	mΩ
I_{RD}	$T_{vj} = 25$ °C; $V_{RD} = V_{RRM}$	max. 2	mA
I_{RD}	$T_{vj} = 150$ °C; $V_{RD} = V_{RRM}$	max. 30	mA
Q_{rr}	$T_{vj} = 125$ °C, $I_F = 330$ A,	80	μC
I_{RM}	-di/dt = 2000 A/μs, $V_R = 1200$ V	220	A
t_{rr}		990	ns
E_{rr}		25	mJ
$R_{th(j-c)}$	DC	0,079	K/W
$R_{th(c-s)}$		0,038	K/W
T_{vj}		- 40 ... + 150	°C
T_{stg}		- 40 ... + 125	°C
V_{isol}	a. c. 50 Hz; r.m.s.; 1 s / 1 min.	4800 / 4000	V~
M_s	to heatsink	3 ... 5	Nm
M_t	to terminals	2,5 ... 5	Nm
a		5 * 9,81	m/s ²
m	approx.	330	g
Case	SEMISTRANS 4	A 68	



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